

SAMSUNG SEMICONDUCTOR INC 14E D 7964142 0007246 1

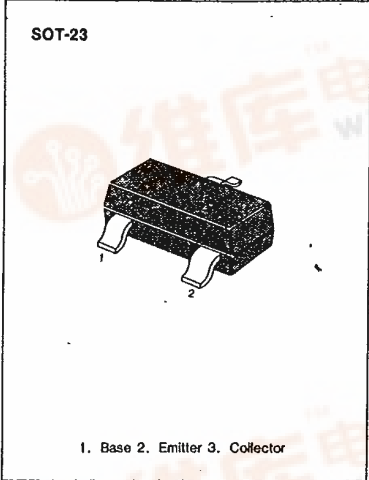
MMBC1623L3 NPN EPITAXIAL SILICON TRANSISTOR

T-29-19-

AMPLIFIER TRANSISTOR

ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)

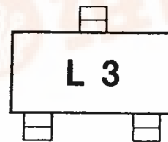
Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Collector Current	I _C	100	mA
Collector Dissipation	P _C	350	mW
Storage Temperature	T _{stg}	150	°C



ELECTRICAL CHARACTERISTICS (T_a = 25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I _{CB0}	V _{CB} = 40V, I _E = 0		100	nA
Emitter Cutoff Current	I _{EBO}	V _{EB} = 5V, I _C = 0		100	nA
DC Current Gain	h _{FE}	V _{CE} = 6V, I _C = 1.0mA	60	120	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = 100mA, I _B = 10mA		0.3	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C = 100mA, I _B = 10mA		1.0	V
Base-Emitter On Voltage	V _{BE(on)}	I _C = 1.0mA, V ₁ = 6V	0.6	0.7	V
Current Gain-Bandwidth Product	f _T	V _{CE} = 6V, I _E = 10mA f = 100MHz	200		MHz

Marking

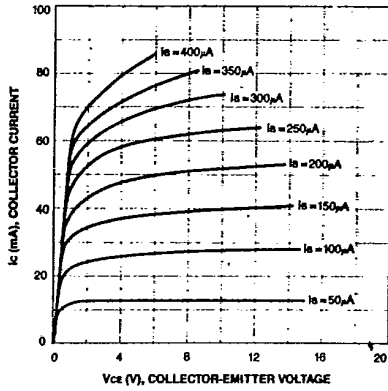


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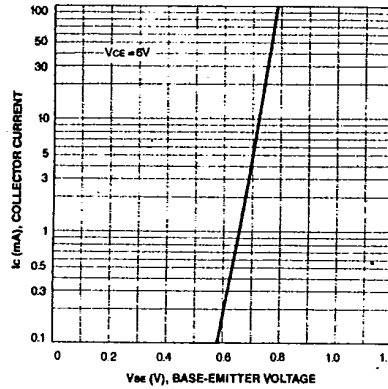
NPN EPITAXIAL SILICON TRANSISTOR

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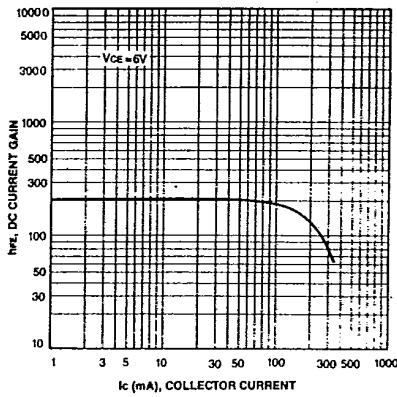
STATIC CHARACTERISTIC



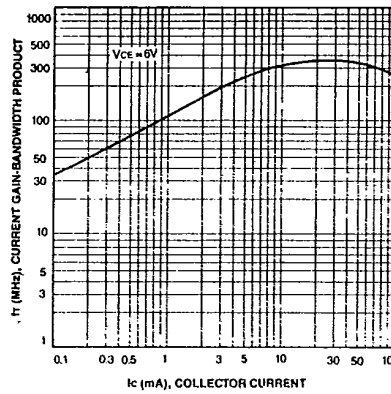
TRANSFER CHARACTERISTIC



DC CURRENT GAIN

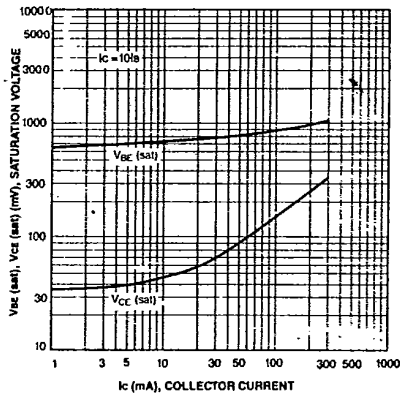


CURRENT GAIN BANDWIDTH PRODUCT



3

BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



OUTPUT CAPACITANCE

